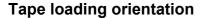


NPN/PNP Silicon Digital Transistor Array

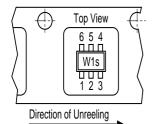
- Switching circuit, inverter, interface circuit, driver circuit
- Two (galvanic) internal isolated NPN/PNP Transistors in one package
- Built in bias resistor NPN and PNP $(R_1=10 \text{ k}\Omega, R_2=10 \text{ k}\Omega)$
- Pb-free (RoHS compliant) package
- Qualified according AEC Q101







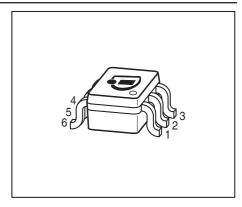
Junction - soldering point¹⁾

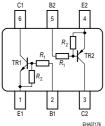


Marking on SOT-363 package (for example W1s) corresponds to pin 1 of device

Position in tape: pin 1 opposite of feed hole side

EHA071





Туре	Marking		Pin Configuration Package					
BCR10PN	W1s	1=E1	2=B1	3=C2	4=E2	5=B2	6=C1	SOT363

Maximum Ratings for NPN and PNP Types

Parameter	Symbol	Value	Unit	
Collector-emitter voltage	$V_{\sf CEO}$	50	V	
Collector-base voltage	V_{CBO}	50		
Input forward voltage	V _{i(fwd)}	40		
Input reverse voltage	V _{i(rev)}	10		
DC collector current	I _C	100	mA	
Total power dissipation, T_S = 115 °C	P _{tot}	250	mW	
Junction temperature	T _j	150	°C	
Storage temperature	T _{stq}	-65 150		

 $^{^{1}}$ For calculation of R_{thJA} please refer to Application Note AN077 (Thermal Resistance Calculation)

K/W

≤ 140

R_{thJS}



Electrical Characteristics at T_A =25°C, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
DC Characteristics for NPN and PNP Types	-				
Collector-emitter breakdown voltage	V _{(BR)CEO}	50	-	-	V
$I_{\rm C}$ = 100 $\mu {\rm A}$, $I_{\rm B}$ = 0					
Collector-base breakdown voltage	V _{(BR)CBO}	50	-	-	
$I_{\rm C} = 10 \ \mu {\rm A}, \ I_{\rm E} = 0$					
Collector cutoff current	I _{CBO}	-	-	100	nA
$V_{\rm CB} = 40 \text{ V}, I_{\rm E} = 0$					
Emitter cutoff current	/ _{EBO}	-	-	0.75	mA
$V_{\rm EB}$ = 10 V, $I_{\rm C}$ = 0					
DC current gain 1)	h _{FE}	30	-	-	-
$I_{\rm C}$ = 5 mA, $V_{\rm CE}$ = 5 V					
Collector-emitter saturation voltage1)	V _{CEsat}	-	-	0.3	V
$I_{\rm C}$ = 10 mA, $I_{\rm B}$ = 0.5 mA					
Input off voltage	$V_{i(off)}$	0.8	-	1.5	
$I_{\rm C}$ = 100 μ A, $V_{\rm CE}$ = 5 V					
Input on Voltage	V _{i(on)}	1	-	2.5	
$I_{\rm C}$ = 2 mA, $V_{\rm CE}$ = 0.3 V					
Input resistor	R ₁	7	10	13	kΩ
Resistor ratio	R_1/R_2	0.9	1	1.1	-
AC Characteristics for NPN and PNP Types					
Transition frequency	f _T	-	130	_	MHz
$I_{\rm C}$ = 10 mA, $V_{\rm CE}$ = 5 V, f = 100 MHz					
Collector-base capacitance	C _{cb}	-	3	-	pF
$V_{\rm CB}$ = 10 V, f = 1 MHz					

2

2011-09-22

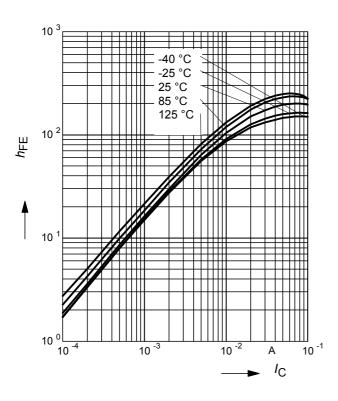
¹⁾ Pulse test: $t < 300\mu s$; D < 2%



NPN Type

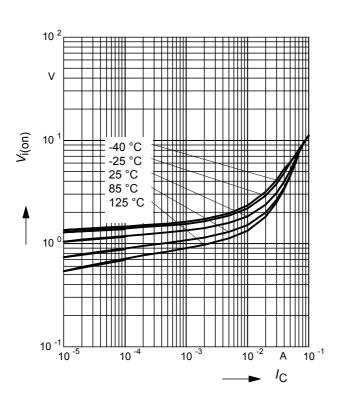
DC Current Gain $h_{FE} = f(I_C)$

 V_{CF} = 5V (common emitter configuration)



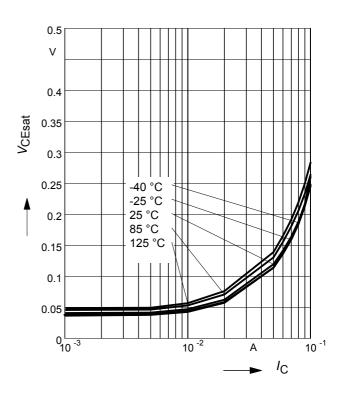
Input on Voltage $V_{i(On)} = f(I_C)$

 V_{CE} = 0.3V (common emitter configuration)



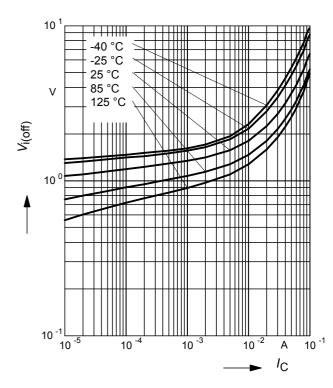
Collector-Emitter Saturation Voltage

 $V_{\text{CEsat}} = f(I_{\text{C}}), h_{\text{FE}} = 20$



Input off voltage $V_{i(Off)} = f(I_C)$

 V_{CE} = 5V (common emitter configuration)

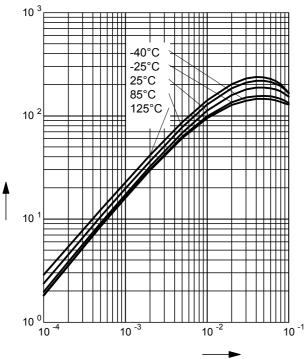




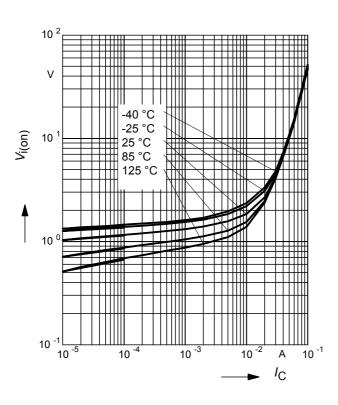
PNP Type

DC Current Gain $h_{FE} = f(I_C)$

 V_{CF} = 5V (common emitter configuration)

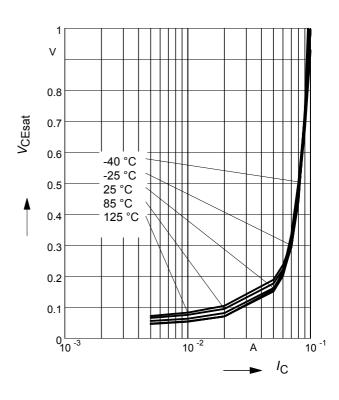


Input on Voltage $V_{i(on)} = f(I_C)$ V_{CE} = 0.3V (common emitter configuration)



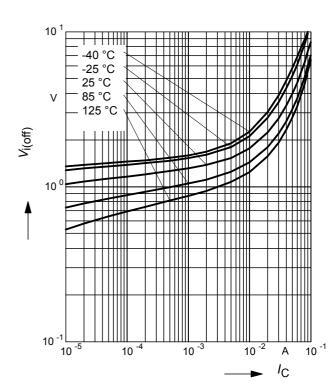
Collector-Emitter Saturation Voltage

 $V_{\text{CEsat}} = f(I_{\text{C}}), h_{\text{FE}} = 20$



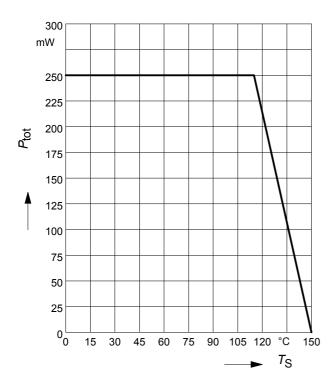
Input off voltage $V_{i(off)} = f(I_C)$

 V_{CE} = 5V (common emitter configuration)



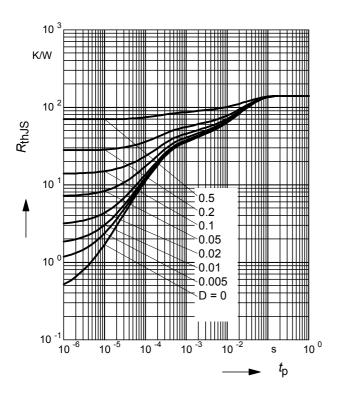


Total power dissipation $P_{tot} = f(T_S)$



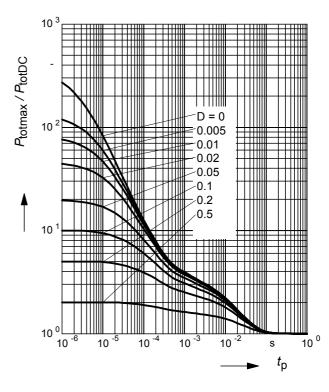
Permissible Pulse Load $R_{thJS} = f(t_p)$

reillissible Pulse Load RthJS - 1 (lp



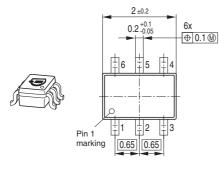
Permissible Pulse Load

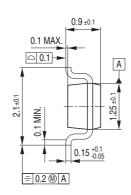
$$P_{\text{totmax}} / P_{\text{totDC}} = f(t_{p})$$



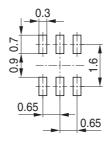


Package Outline



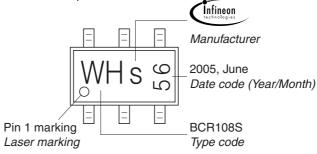


Foot Print



Marking Layout (Example)

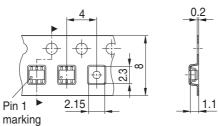
Small variations in positioning of Date code, Type code and Manufacture are possible.



Standard Packing

Reel ø180 mm = 3.000 Pieces/Reel Reel ø330 mm = 10.000 Pieces/Reel

For symmetric types no defined Pin 1 orientation in reel.



6



Edition 2009-11-16

Published by Infineon Technologies AG 81726 Munich, Germany

© 2009 Infineon Technologies AG All Rights Reserved.

Legal Disclaimer

The information given in this document shall in no event be regarded as a guarantee of conditions or characteristics. With respect to any examples or hints given herein, any typical values stated herein and/or any information regarding the application of the device, Infineon Technologies hereby disclaims any and all warranties and liabilities of any kind, including without limitation, warranties of non-infringement of intellectual property rights of any third party.

Information

For further information on technology, delivery terms and conditions and prices, please contact the nearest Infineon Technologies Office (www.infineon.com).

Warnings

Due to technical requirements, components may contain dangerous substances. For information on the types in question, please contact the nearest Infineon Technologies Office.

Infineon Technologies components may be used in life-support devices or systems only with the express written approval of Infineon Technologies, if a failure of such components can reasonably be expected to cause the failure of that life-support device or system or to affect the safety or effectiveness of that device or system. Life support devices or systems are intended to be implanted in the human body or to support and/or maintain and sustain and/or protect human life. If they fail, it is reasonable to assume that the health of the user or other persons may be endangered.

7

2011-09-22

X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for Bipolar Transistors - Pre-Biased category:

Click to view products by Infineon manufacturer:

Other Similar products are found below:

RN1607(TE85L,F) DTA124GKAT146 DTA144WETL DTA144WKAT146 DTC113EET1G DTC115TETL DTC115TKAT146

DTC124TETL DTC144ECA-TP DTC144VUAT106 MUN5241T1G NSBA114TDP6T5G NSBA143ZF3T5G NSBC114YF3T5G

NSBC123TF3T5G SMUN5235T1G SMUN5330DW1T1G SSVMUN5312DW1T2G RN1303(TE85L,F) RN4605(TE85L,F)

TTEPROTOTYPE79 DDTC114EUAQ-7-F EMH15T2R SMUN2214T3G NSBC114TF3T5G NSBC143ZPDP6T5G

NSVMUN5113DW1T3G SMUN5230DW1T1G SMUN5133T1G SMUN2214T1G DTC114EUA-TP NSBA144EF3T5G

NSVDTA114EET1G 2SC2223-T1B-A 2SC3912-TB-E SMUN5237DW1T1G SMUN5213DW1T1G SMUN5114DW1T1G SMUN2111T1G

NSVDTC144EM3T5G DTC124ECA-TP DTC123TM3T5G DTA114ECA-TP DTA113EM3T5G DCX115EK-7-F DTC113EM3T5G

NSVMUN5135DW1T1G NSVDTC143ZM3T5G SMUN5216DW1T1G NSVMUN5312DW1T2G